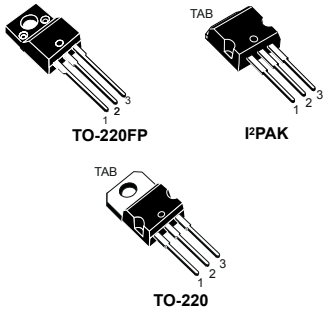
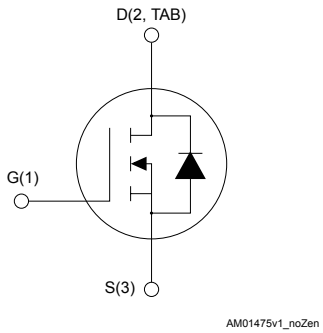
STF24NM60N, STI24NM60N, STP24NM60N

Datasheet

N-channel 600 V, 168 mΩ typ., 17 A MDmesh II Power MOSFET in a TO-220FP, I²PAK and TO-220 packages





Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STF24NM60N	600 V	190 mΩ	17 A
STI24NM60N			
STP24NM60N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh technology. These revolutionary Power MOSFETs associate a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. They are therefore suitable for the most demanding high-efficiency converters.

STPOWER

Product status links
STF24NM60N
STI24NM60N
STP24NM60N

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		I^2PAK TO-220	TO-220FP	
V_{DS}	Drain-source voltage	600		V
V_{GS}	Gate-source voltage	±30		V
I_D	Drain current (continuous) at T_C = 25 °C	17		A
I_D	Drain current (continuous) at T_C = 100 °C	11		A
I_{DM}(1)	Drain current (pulsed)	68		A
P_{TOT}	Total power dissipation at T_C = 25 °C	125	30	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T_C = 25 °C)	-	2.5	kV
dv/dt(2)	Peak diode recovery voltage slope	15		V/ns
T_{stg}	Storage temperature range	-55 to 150		°C
T_J	Operating junction temperature range			°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 17 A, di/dt ≤ 400 A/µs, V_{DS} (peak) ≤ $V_{(BR)DSS}$, V_{DD} = 480 V.*

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		I^2PAK	TO-220	TO-220FP	
R_{thJC}	Thermal resistance, junction-to-case	1		4.17	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	62.5			°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	6	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	300	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	600	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V	-	-	1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)	-	-	100	
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V	-	-	±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 8 A	-	168	190	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0 V	-	1330	-	pF
C_{oss}	Output capacitance		-	80	-	pF
C_{rss}	Reverse transfer capacitance		-	3.2	-	pF
$C_{oss\ eq.}$(1)	Equivalent capacitance time related	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	182	-	pF
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 17 A, V_{GS} = 0 to 10 V (see the Figure 16. Test circuit for gate charge behavior)	-	44	-	nC
Q_{gs}	Gate-source charge		-	7	-	nC
Q_{gd}	Gate-drain charge		-	24	-	nC
R_g	Intrinsic gate resistance	f = 1 MHz open drain	-	5	-	Ω

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 8.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see the Figure 15. Test circuit for resistive load switching times and Figure 20. Switching time waveform)	-	11.5	-	ns
t_r	Rise time		-	16.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	73	-	ns
t_f	Fall time		-	37	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	17	A
I_{SDM}(1)	Source-drain current (pulsed)		-	-	68	A
V_{SD}(2)	Forward on voltage	I_{SD} = 17 A, V_{GS} = 0 V	-	-	1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 17 A, di/dt = 100 A/µs, V_{DD} = 60 V (see the Figure 17. Test circuit for inductive load switching and diode recovery times)	-	340	-	ns
Q_{rr}	Reverse recovery charge		-	4.6	-	µC
I_{RRM}	Reverse recovery current		-	27	-	A
t_{rr}	Reverse recovery time	I_{SD} = 17 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_J = 150 °C (see the Figure 17. Test circuit for inductive load switching and diode recovery times)	-	404	-	ns
Q_{rr}	Reverse recovery charge		-	5.7	-	µC
I_{RRM}	Reverse recovery current		-	28	-	A

1. *Pulse width limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220FP

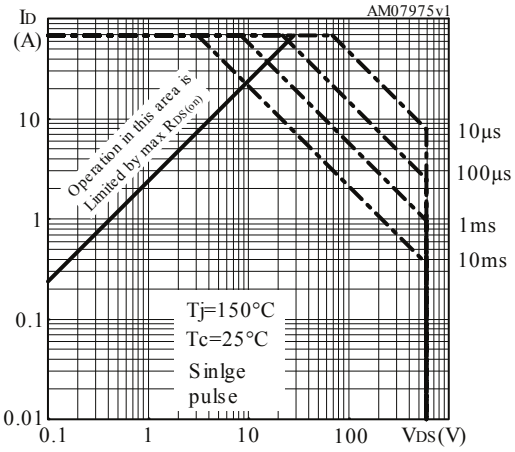


Figure 2. Normalized transient thermal impedance for TO-220FP

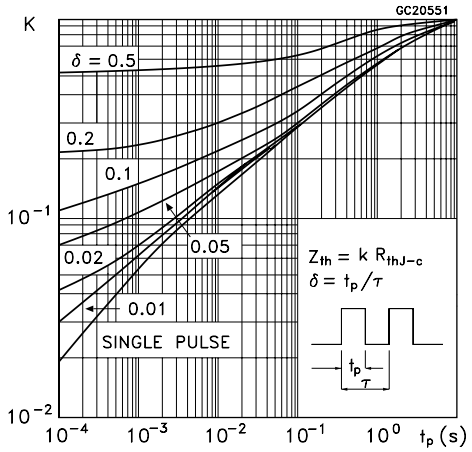


Figure 3. Safe operating area for I²PAK and TO-220

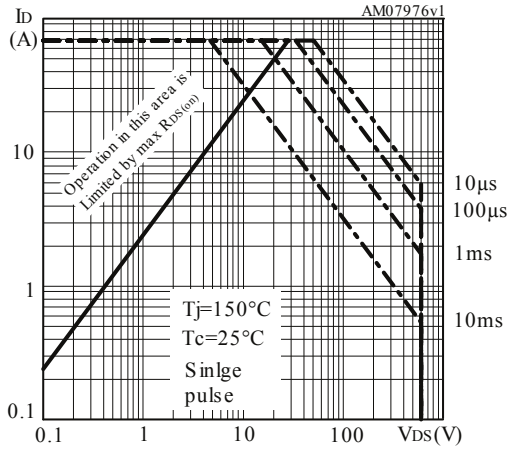


Figure 4. Normalized transient thermal impedance for I²PAK and TO-220

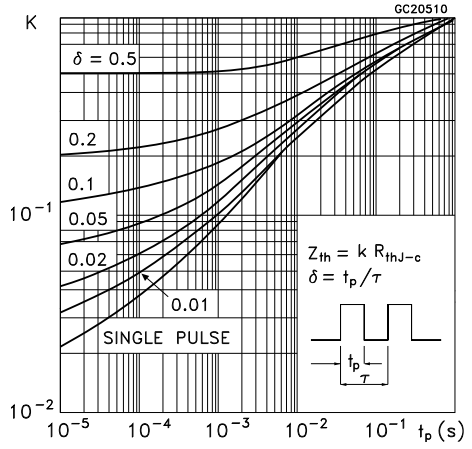


Figure 5. Typical output characteristics

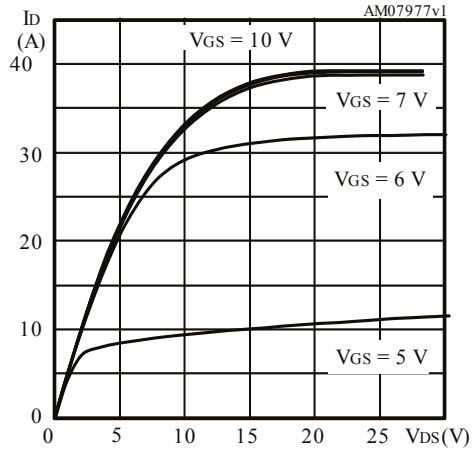


Figure 6. Typical transfer characteristics

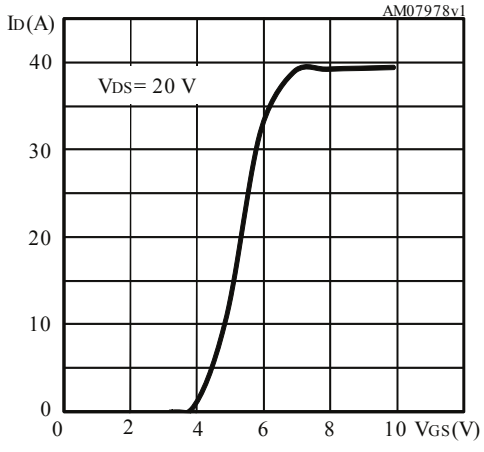


Figure 7. Typical gate charge characteristics

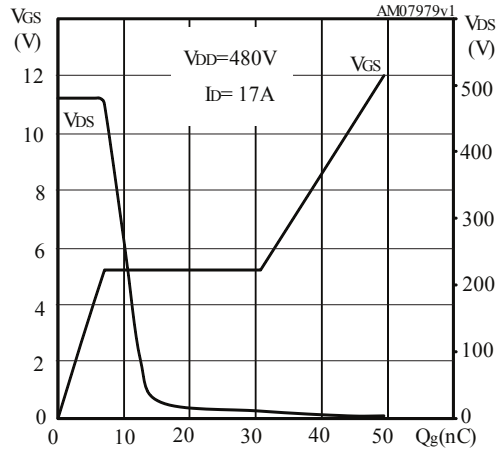


Figure 8. Typical capacitance characteristics

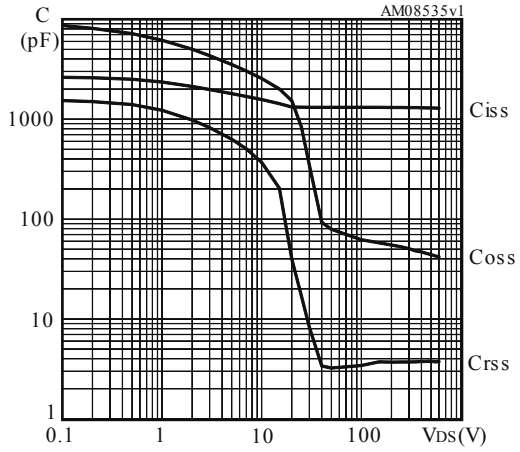


Figure 9. Typical drain-source on-resistance

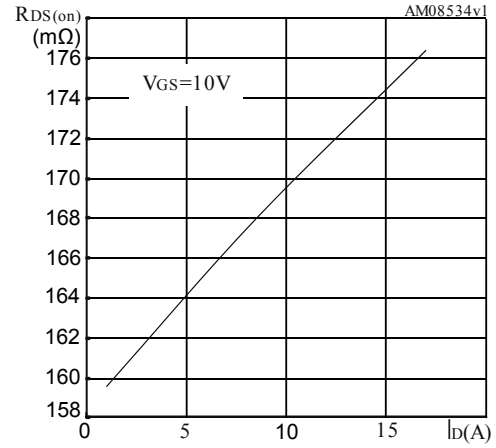


Figure 10. Typical output capacitance stored energy

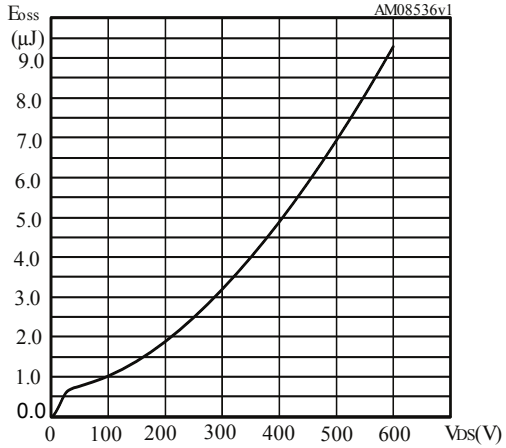


Figure 11. Normalized gate threshold vs temperature

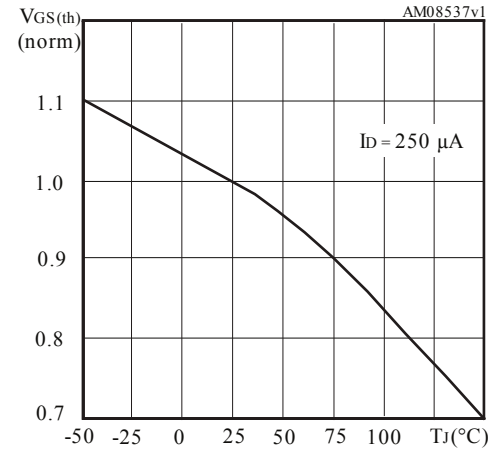


Figure 12. Normalized on-resistance vs temperature

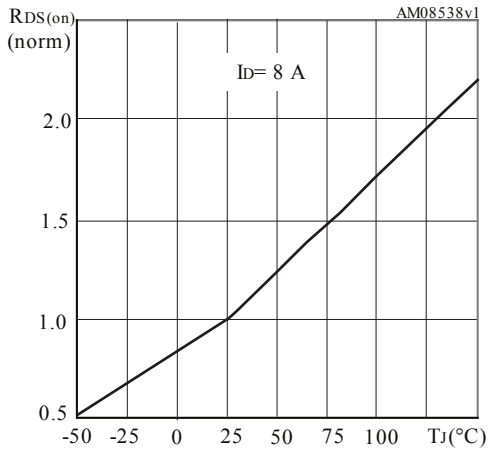


Figure 13. Normalized breakdown voltage vs temperature

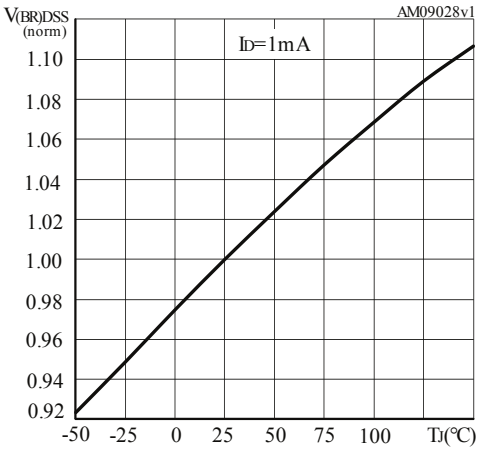
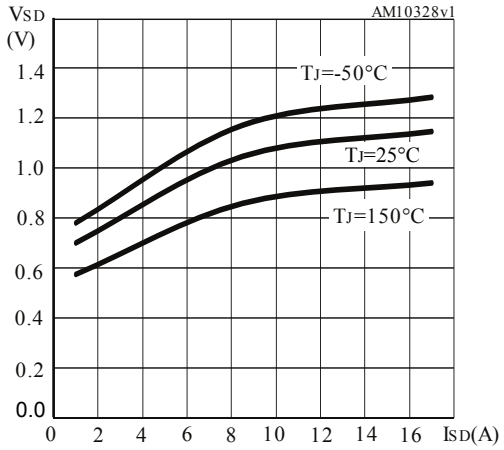


Figure 14. Typical reverse diode forward characteristics



3 Test circuits

Figure 15. Test circuit for resistive load switching times

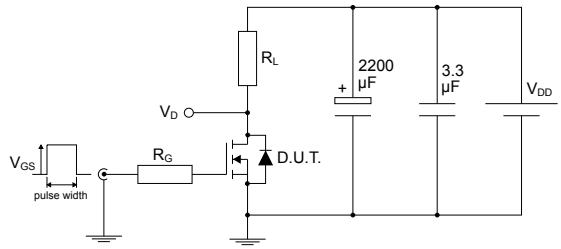


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Figure 16. Test circuit for gate charge behavior

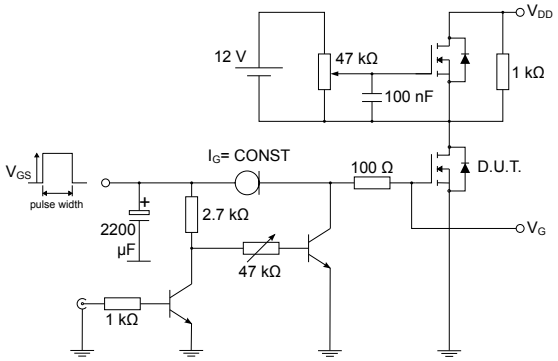

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Figure 17. Test circuit for inductive load switching and diode recovery times

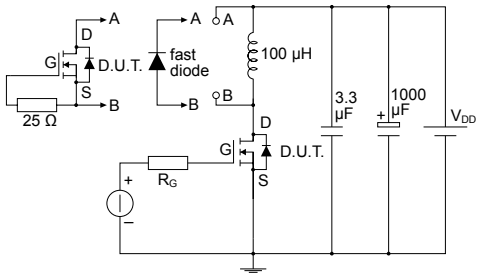

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Figure 18. Unclamped inductive load test circuit

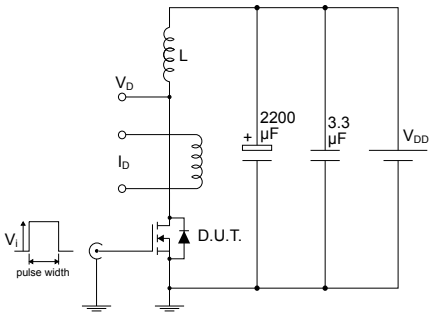

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Figure 19. Unclamped inductive waveform

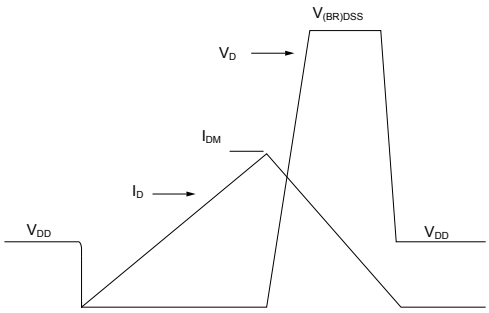

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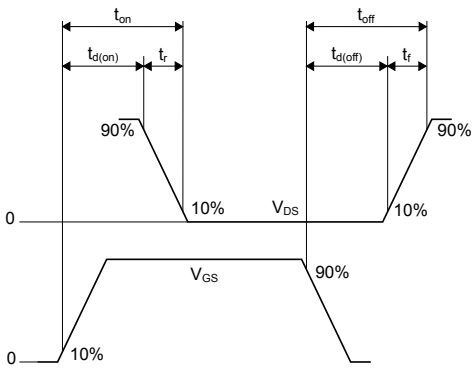
Figure 20. Switching time waveform



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4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP type B package information

Figure 21. TO-220FP type B package outline

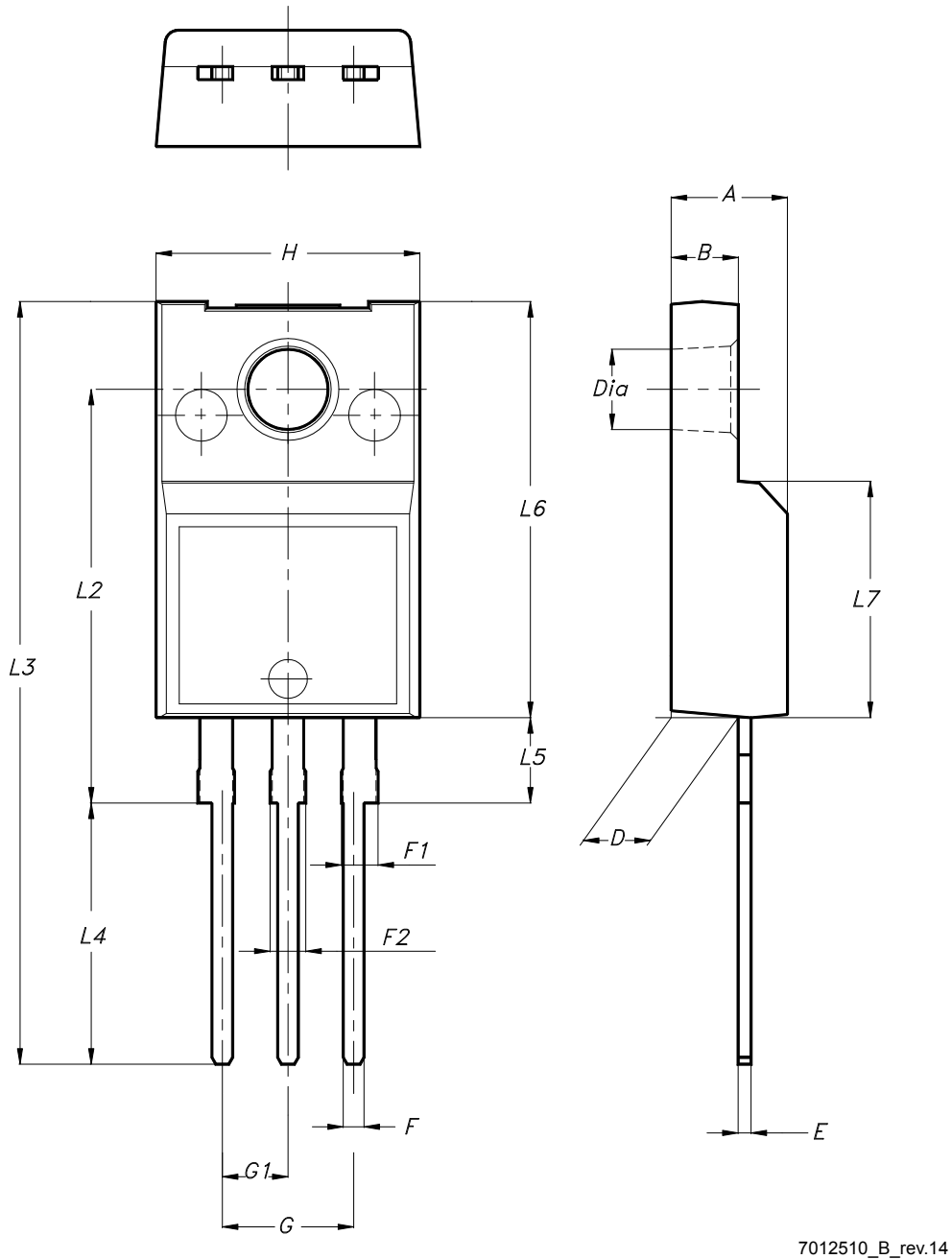

Table 8. **TO-220FP type B package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.2 I²PAK package information

Figure 22. I²PAK package outline

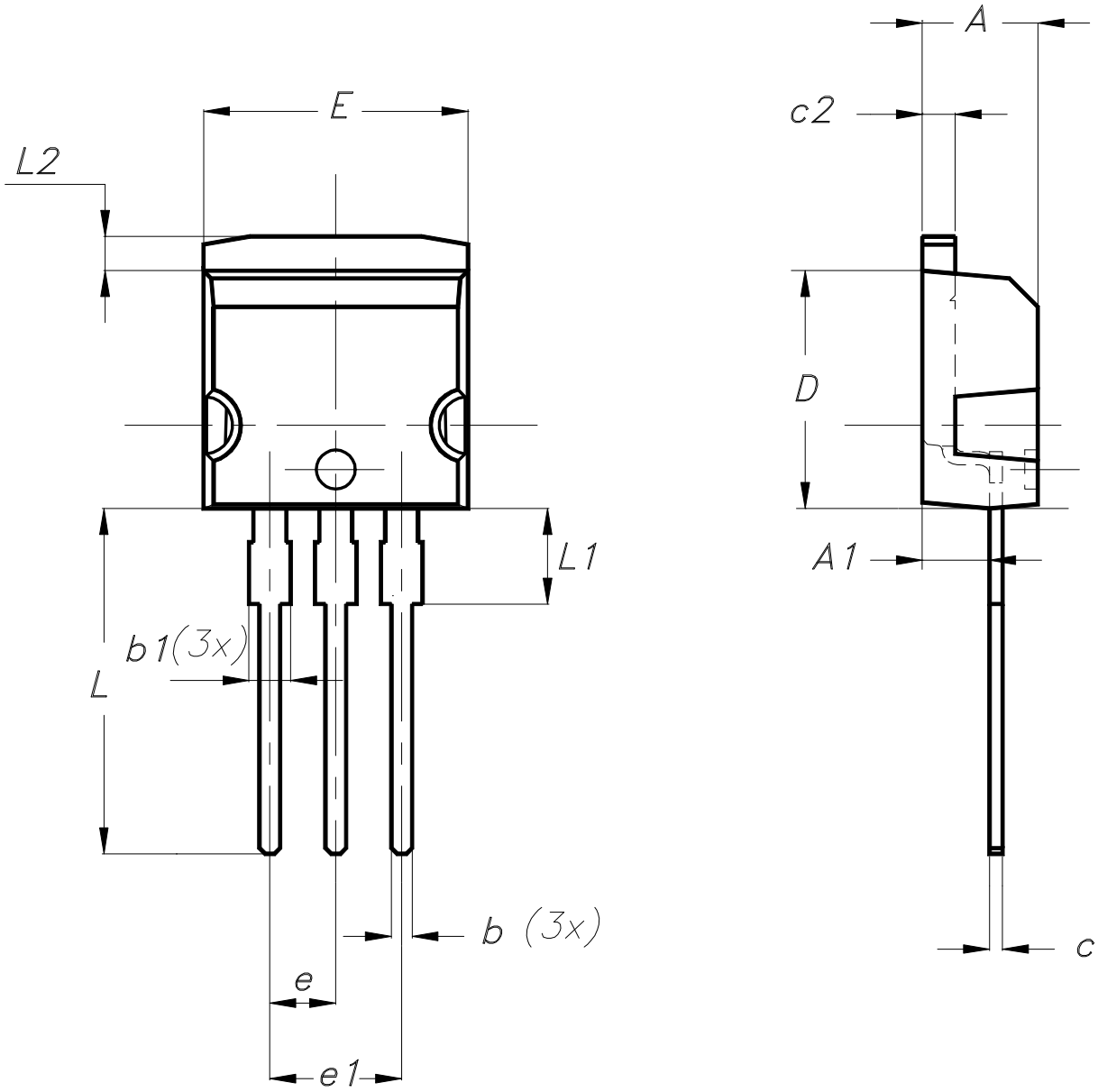

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Table 9. I²PAK package mechanical data

Dim.	mm	
	Min.	Max.
A	4.40	4.60
A1	2.40	2.72
b	0.61	0.88
b1	1.14	1.70
c	0.49	0.70
c2	1.23	1.32
D	8.95	9.35
e	2.40	2.70
e1	4.95	5.15
E	10.00	10.40
L	13.00	14.00
L1	3.50	3.93
L2	1.27	1.40

4.3 TO-220 type A package information

Figure 23. **TO-220 type A package outline**

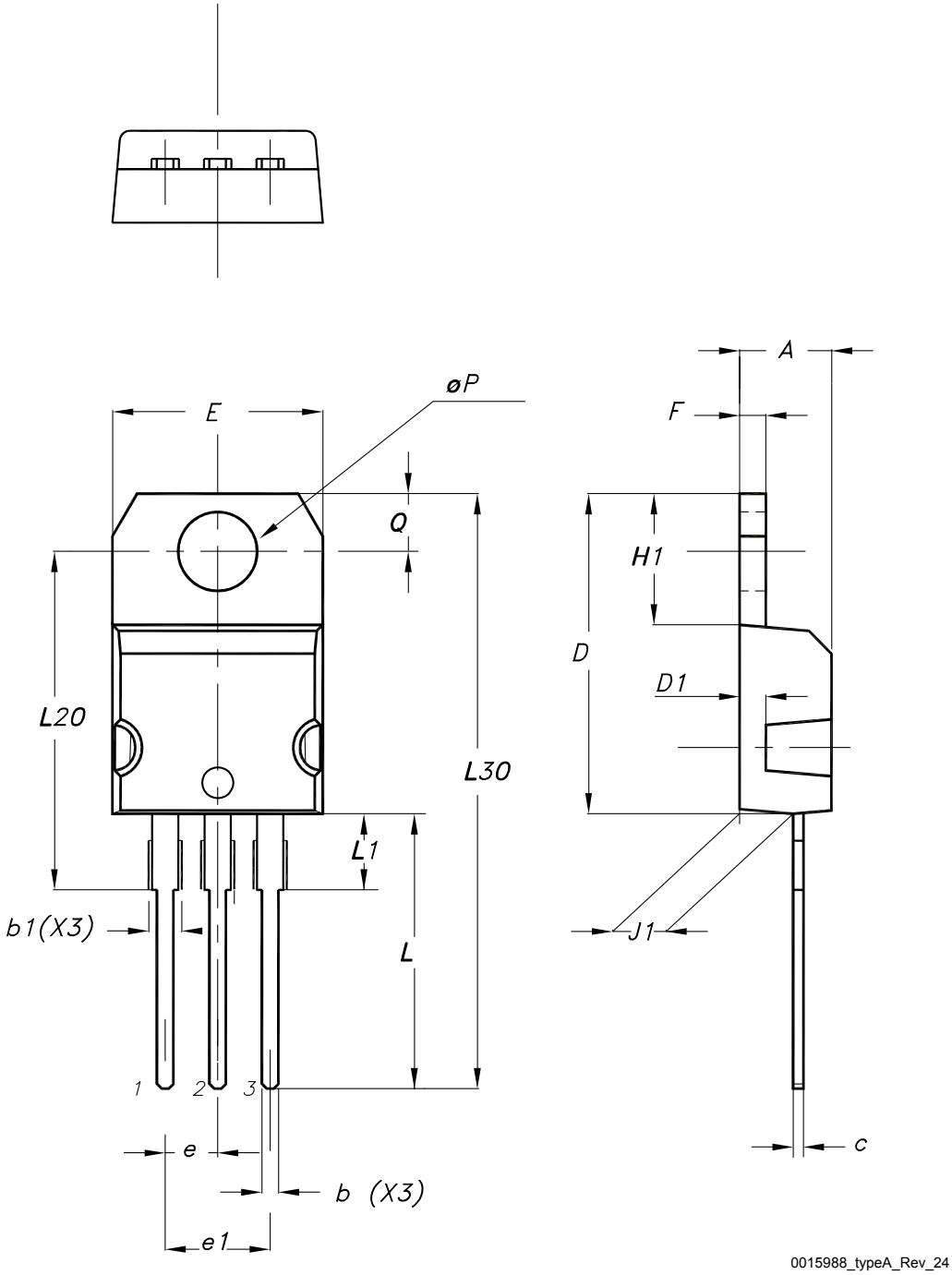

Table 10. **TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

5 Ordering information

Table 11. **Order codes**

Order codes	Marking	Package	Packing
STF24NM60N	24NM60N	TO-220FP	Tube
STI24NM60N		I²PAK	
STP24NM60N		TO-220	

Revision history

Table 12. **Document revision history**

Date	Revision	Changes
05-Jan-2011	1	First release.
01-Jul-2011	2	Corrected $R_{thj\text{-}amb}$ value (see *Table 3: Thermal data*). Added new package and mechanical data: TO-247.
22-Aug-2011	3	Inserted device in I^2PAK. Updated *Table 1: Device summary*, *Table 2: Absolute maximum ratings* and *Table 3: Thermal data*. Inserted new mechanical data in *Section 4: Package mechanical data*.
24-Jul-2014	4	Modified: the entire typical values in *Table 6*. Modified: *Figure 12*. Updated: *Section 4: Package mechanical data*. Minor text changes.
13-Jan-2026	5	Removed order code STW24NM60N. Updated Section 4: Package information. Minor text changes.

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